

UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/736,063	12/15/2003	Young-Hun Seo	OPP031058US	4273
36872	7590 07/26/2006		EXAMINER	
THE LAW OFFICES OF ANDREW D. FORTNEY, PH.D., P.C.			MITCHELL, JAMES M	
	401 W FALLBROOK AVE STE 204 FRESNO, CA 93711-5835		ART UNIT	PAPER NUMBER
,			2813	
			DATE MAILED: 07/26/200	6

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summary		10/736,063	SEO, YOUNG-HUN			
		Examiner	Art Unit			
		James M. Mitchell	2813			
Period fo	The MAILING DATE of this communication a	ppears on the cover sheet with the	correspondence address			
	•	LVIC CET TO EVOIDE A MONTH	U(C) OR THIRTY (20) DAYO			
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REP CHEVER IS LONGER, FROM THE MAILING Insions of time may be available under the provisions of 37 CFR 1 SIX (6) MONTHS from the mailing date of this communication. In period for reply is specified above, the maximum statutory perior to reply within the set or extended period for reply will, by stature to received by the Office later than three months after the mailed patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICATION IN THE PROPERTY IN THE PROPERTY OF	ON. timely filed om the mailing date of this communication. NED (35 U.S.C. § 133).			
Status						
1)⊠	Responsive to communication(s) filed on 05	April 2006.				
· —		is action is non-final.				
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
	closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 11,	453 O.G. 213.			
Dispositi	on of Claims					
4)🖂	4)⊠ Claim(s) <u>1-12 and 14-21</u> is/are pending in the application.					
	4a) Of the above claim(s) is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.						
6)⊠	6)⊠ Claim(s) <u>1-12 and 14-21</u> is/are rejected.					
7)	Claim(s) is/are objected to.					
8)[Claim(s) are subject to restriction and/	or election requirement.				
Applicati	on Papers					
9)	The specification is objected to by the Examir	ner.				
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.						
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11)	The oath or declaration is objected to by the E	Examiner. Note the attached Office	ce Action or form PTO-152.			
Priority ι	ınder 35 U.S.C. § 119					
12)⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a)⊠ All b)□ Some * c)□ None of:						
	1.⊠ Certified copies of the priority documents have been received.					
	2. Certified copies of the priority documents have been received in Application No					
	3. Copies of the certified copies of the priority documents have been received in this National Stage					
* C	application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.					
3	see the attached detailed Office action for a lis	at of the certified copies not receive	vea.			
Attachmen	•	_				
	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948)	4)				
3) 🔲 Inforr	nation Disclosure Statement(s) (PTO-1449 or PTO/SB/08 r No(s)/Mail Date	_	Patent Application (PTO-152)			

Application/Control Number: 10/736,063

Art Unit: 2813

DETAILED ACTION

This office action is in response to applicant's request for continued examination filed April 5, 2006.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1, 2, 5, 8, 11, 12 and 14-21 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ahn (U.S. 5,612,237) in combination Rhodes (U.S. 2004/0094784).

Ahn (Fig. 3A-F) discloses:

(cl. 1) a method of forming a gate in a semiconductor device, the method comprising: forming a trench (e.g. groove in substrate; Fig. 3C); forming a gate oxide layer (25) on the semiconductor substrate; forming on the semiconductor substrate a sacrificial layer (23) selectively etching the sacrificial layer to form sidewall openings over an area of the substrate including the trench (Fig. 3C); forming a polycrystalline silicon layer (26) on the area of the gate oxide exposed through the sidewall opening and on the sacrificial layer; etching (Abstract) of polycrystalline silicon layer such the sidewall gates (26A,B) on sidewall opening (Fig. 3E); and removing the sacrificial layer (Fig. 3F);

- (cl. 2, 8) wherein the sacrificial layer comprises nitride Abstract);
- (cl. 6, 12) where the thickness of sacrificial determines/affects width of gates (Fig 3D-E);

Application/Control Number: 10/736,063

Art Unit: 2813

(cl. 7) wherein width of opening (e.g. both gates in opening space) corresponds to a width from one gate to an adjacent gate (Fig. 3D-3E);

(cl. 14) wherein width of the sidewall gates corresponds to a desired width of a gate (e.g. to be functional);

(cl. 15, 16, 17) wherein etch back includes etching gates to a minimum width (e.g. the width predetermined);

(cl. 18, 19) further depositing a photoresist (30) on the sacrificial layer (23)a and pattering to form an opening exposing a predetermined area the sacrificial layer (Fig. 3A);

(cl. 20, 21) wherein the opening comprises/ encompasses an area on the substrate from where one sidewall gate will be formed to where an adjacent gate will be formed (Fig. 3C-E);

Ahn further shows a dry etch, but does not appear to explicitly disclose that it is anisotropically or an etch back process.

Rhodes utilizes a dry anisotropic etch (Par. 0010) that comprises an etch back¹.

It would have been obvious to one of ordinary skill in the art to incorporate an anisotropic etch as the etch process disclosed by Ahn in order to provide a dry etch as required by Ahn (Col. 3, Lines 24-26).

¹ Applicant CLAIM 5 admits that an anisotropic etch comprises etch back.

Art Unit: 2813

Claims 3, 4, 9 and 10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ahn (U.S. 5,612,237) and Rhodes (U.S. 2004/0094784) as applied to claim 1, 2, 7 or 8, and in further combination with Kim et al. (U.S. 20025/0001935).

Neither Ahn nor Rhodes appear to show that its etch is wet etching,

However Ahn discloses the same invention except that it teaches a dry etch instead of a wet etch, Kim shows that either a wet or dry etch are equivalent processes that form the same structure known in the art. Therefore, because these processes are art recognized equivalents at the time the invention was made, one of ordinary skill in the art would have found it obvious to substitute a process of using a wet etch instead of a dry etch to remove material.²

Response to Arguments

Applicant's arguments with respect to claims have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to James M. Mitchell whose telephone number is (571) 272-1931. The examiner can normally be reached on M-F 8:00-4:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on (571) 272-1702. The fax phone

² Likewise, Rhodes (Par. 0010) discloses that "other etching process" may be used.

Art Unit: 2813

number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Jmm, J.D July 2012/006

CARL WHITEHEAD, JK.

SUPERVISORY PATENT EXAMINER

TECHNOLOGY CENTER 2800